

INFORMATION DISCLOSURE CITATION

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Applicants Katsuhiko HIEDA et al.	
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U.S. PATENT DOCUMENTS							
Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
Bj		6,191,002	02/20/01	Koyanagi			

FOREIGN PATENT DOCUMENTS							
		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
Bj	Heo et al., "Void Free and Low Stress Shallow Trench Isolation Technology Using P-SOG For Sub 0.1 μ m Device", 2002 Symposium On VLSI Technology Digest of Technical Papers, pp. 132-133, 2002.

Examiner Bin h Tran	Date Considered 8/24/05
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